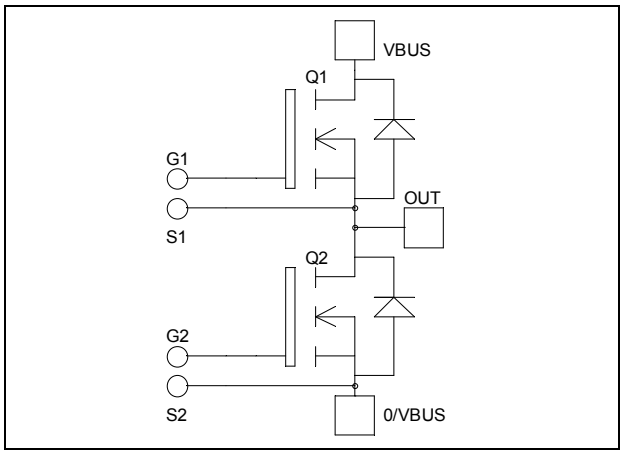
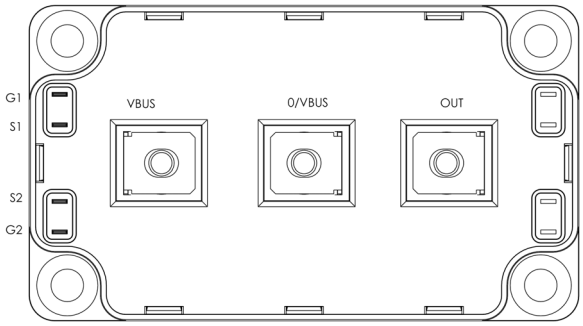
# APTM100AM90FG

## *Phase leg MOSFET Power Module*

$V_{DSS}$ = 1000V
$R_{DSon}$ = 90mΩ typ @ Tj = 25°C
$I_D$ = 78A @ Tc = 25°C




### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Power MOS 7® FREDFETs
  - Low $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

## Absolute maximum ratings

| *Symbol* | *Parameter* | | *Max ratings* | *Unit* |
|---|---|---|---|---|
| $V_{DSS}$ | Drain - Source Breakdown Voltage | | 1000 | V |
| $I_D$ | Continuous Drain Current | $T_c$ = 25°C | 78 | A |
| | | $T_c$ = 80°C | 59 | |
| $I_{DM}$ | Pulsed Drain current | | 312 | |
| $V_{GS}$ | Gate - Source Voltage | | ±30 | V |
| $R_{DSon}$ | Drain - Source ON Resistance | | 105 | mΩ |
| $P_D$ | Maximum Power Dissipation | $T_c$ = 25°C | 1250 | W |
| $I_{AR}$ | Avalanche current (repetitive and non repetitive) | | 25 | A |
| $E_{AR}$ | Repetitive Avalanche Energy | | 50 | mJ |
| $E_{AS}$ | Single Pulse Avalanche Energy | | 3000 | |

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

**All ratings @ $T_j$ = 25°C unless otherwise specified**

## Electrical Characteristics

| *Symbol* | *Characteristic* | *Test Conditions* | | *Min* | *Typ* | *Max* | *Unit* |
|---|---|---|---|---|---|---|---|
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{GS}$ = 0V, $V_{DS}$ = 1000V | $T_j$ = 25°C | | | 400 | µA |
| | | $V_{GS}$ = 0V, $V_{DS}$ = 800V | $T_j$ = 125°C | | | 2000 | |
| $R_{DS(on)}$ | Drain – Source on Resistance | $V_{GS}$ = 10V, $I_D$ = 39A | | | 90 | 105 | mΩ |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 10mA | | 3 | | 5 | V |
| $I_{GSS}$ | Gate – Source Leakage Current | $V_{GS}$ = ±30 V, $V_{DS}$ = 0V | | | | ±250 | nA |

## Dynamic Characteristics

| *Symbol* | *Characteristic* | *Test Conditions* | *Min* | *Typ* | *Max* | *Unit* |
|---|---|---|---|---|---|---|
| $C_{iss}$ | Input Capacitance | $V_{GS}$ = 0V<br>$V_{DS}$ = 25V<br>f = 1MHz | | 20.7 | | nF |
| $C_{oss}$ | Output Capacitance | | | 3.5 | | |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 0.64 | | |
| $Q_g$ | Total gate Charge | $V_{GS}$ = 10V<br>$V_{Bus}$ = 500V<br>$I_D$ = 78A | | 744 | | nC |
| $Q_{gs}$ | Gate – Source Charge | | | 96 | | |
| $Q_{gd}$ | Gate – Drain Charge | | | 488 | | |
| $T_{d(on)}$ | Turn-on Delay Time | **Inductive switching @ 125°C**<br>$V_{GS}$ = 15V<br>$V_{Bus}$ = 670V<br>$I_D$ = 78A<br>$R_G$ =1.2Ω | | 18 | | ns |
| $T_r$ | Rise Time | | | 12 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | 155 | | |
| $T_f$ | Fall Time | | | 40 | | |
| $E_{on}$ | Turn-on Switching Energy | **Inductive switching @ 25°C**<br>$V_{GS}$ = 15V, $V_{Bus}$ = 670V<br>$I_D$ = 78A, $R_G$ = 1.2Ω | | 3.6 | | mJ |
| $E_{off}$ | Turn-off Switching Energy | | | 2.5 | | |
| $E_{on}$ | Turn-on Switching Energy | **Inductive switching @ 125°C**<br>$V_{GS}$ = 15V, $V_{Bus}$ = 670V<br>$I_D$ = 78A, $R_G$ = 1.2Ω | | 5.7 | | mJ |
| $E_{off}$ | Turn-off Switching Energy | | | 3.1 | | |

## Source - Drain diode ratings and characteristics

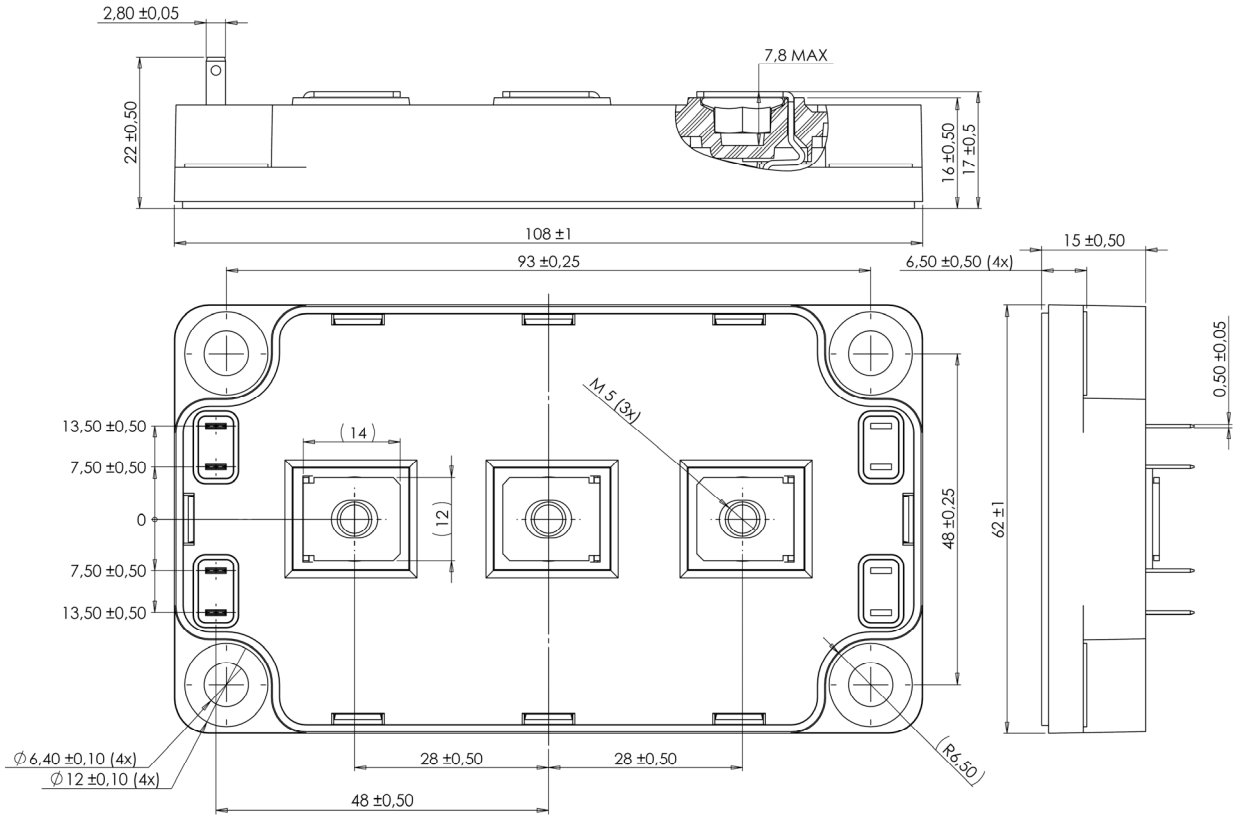
| *Symbol* | *Characteristic* | *Test Conditions* | | *Min* | *Typ* | *Max* | *Unit* |
|---|---|---|---|---|---|---|---|
| $I_S$ | Continuous Source current (Body diode) | | Tc = 25°C | | | 78 | A |
| | | | Tc = 80°C | | | 59 | |
| $V_{SD}$ | Diode Forward Voltage | $V_{GS}$ = 0V, $I_S$ = - 78A | | | | 1.3 | V |
| dv/dt | Peak Diode Recovery ❶ | | | | | 18 | V/ns |
| $t_{rr}$ | Reverse Recovery Time | $I_S$ = - 78A<br>$V_R$ = 670V<br>$di_S/dt$ = 400A/µs | $T_j$ = 25°C | | | 320 | ns |
| | | | $T_j$ = 125°C | | | 650 | |
| $Q_{rr}$ | Reverse Recovery Charge | | $T_j$ = 25°C | | 14.4 | | µC |
| | | | $T_j$ = 125°C | | 38.9 | | |

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.
$I_S \le$ - 78A  di/dt ≤ 700A/µs  $V_R \le V_{DSS}$  $T_j \le$ 150°C

## Thermal and package characteristics

| *Symbol* | *Characteristic* | | | *Min* | *Typ* | *Max* | *Unit* |
|---|---|---|---|---|---|---|---|
| $R_{thJC}$ | Junction to Case Thermal Resistance | | | | | 0.1 | °C/W |
| $V_{ISOL}$ | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz | | | 4000 | | | V |
| $T_J$ | Operating junction temperature range | | | -40 | | 150 | °C |
| $T_{STG}$ | Storage Temperature Range | | | -40 | | 125 | |
| $T_C$ | Operating Case Temperature | | | -40 | | 100 | |
| Torque | Mounting torque | To heatsink | M6 | 3 | | 5 | N.m |
| | | For terminals | M5 | 2 | | 3.5 | |
| Wt | Package Weight | | | | | 300 | g |

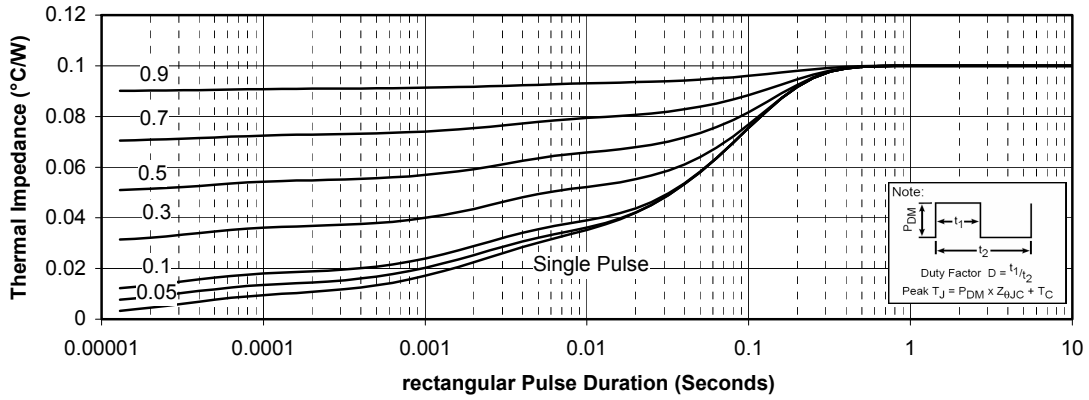
## SP6 Package outline (dimensions in mm)



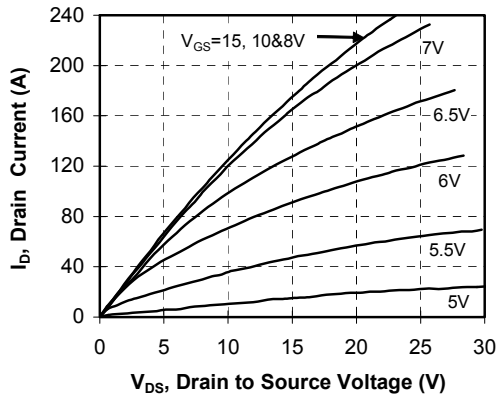

See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

## Typical Performance Curve

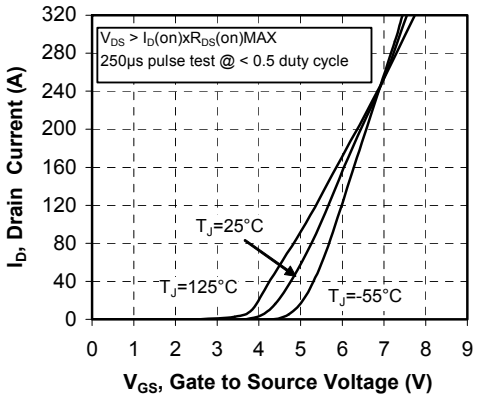
**Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration**



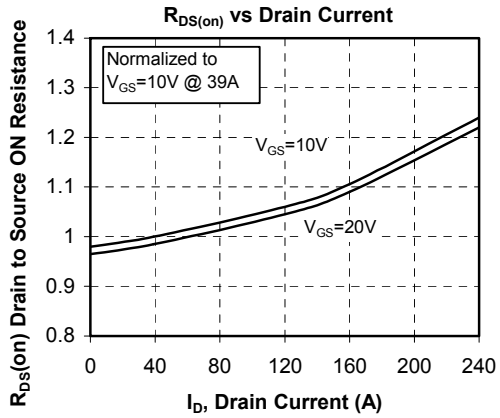

**Low Voltage Output Characteristics**



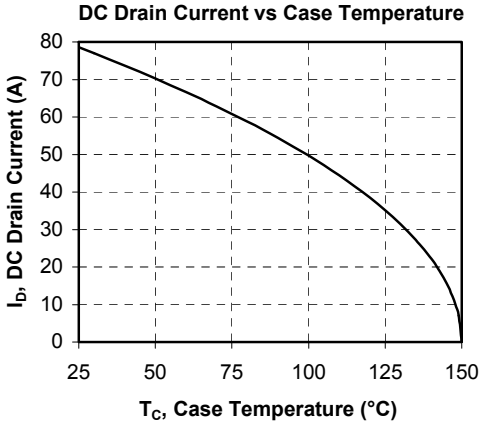

**Transfert Characteristics**



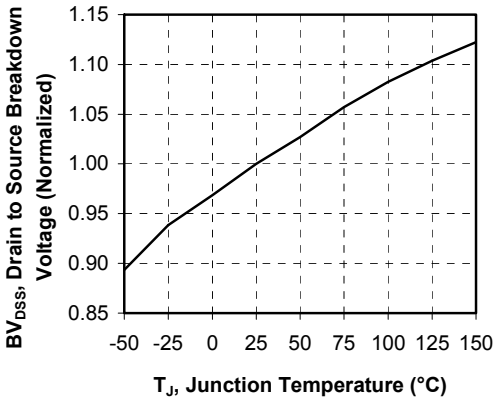

**$R_{DS(on)}$ vs Drain Current**



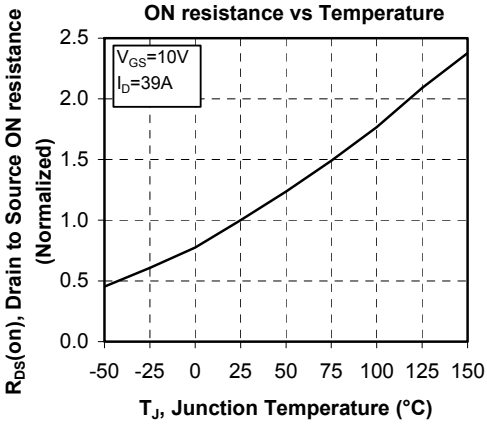

**DC Drain Current vs Case Temperature**



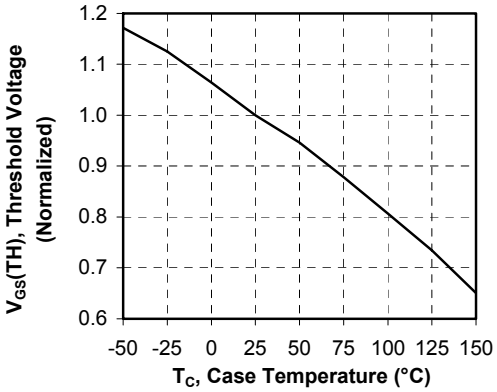
**Breakdown Voltage vs Temperature**



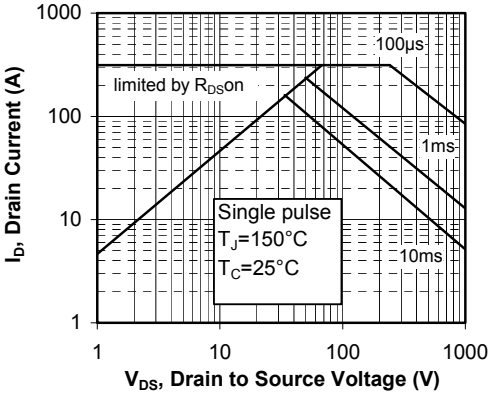

**ON resistance vs Temperature**



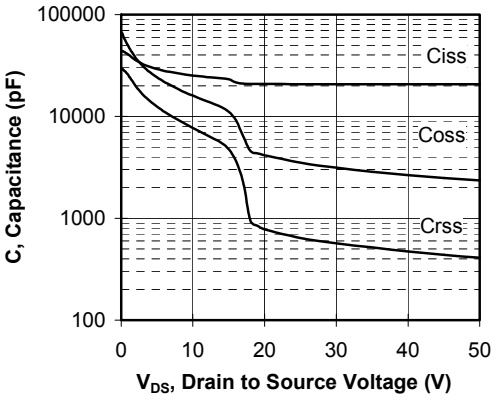

**Threshold Voltage vs Temperature**



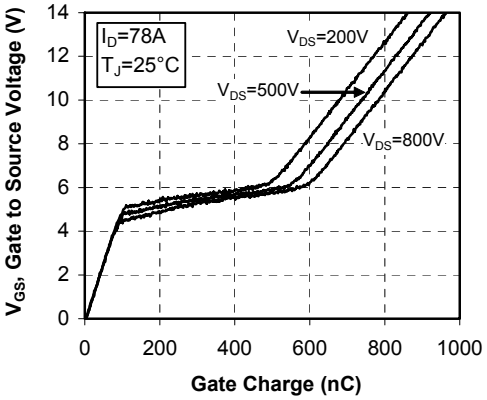

**Maximum Safe Operating Area**



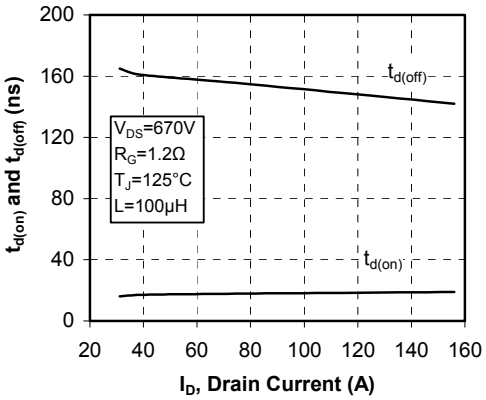

**Capacitance vs Drain to Source Voltage**



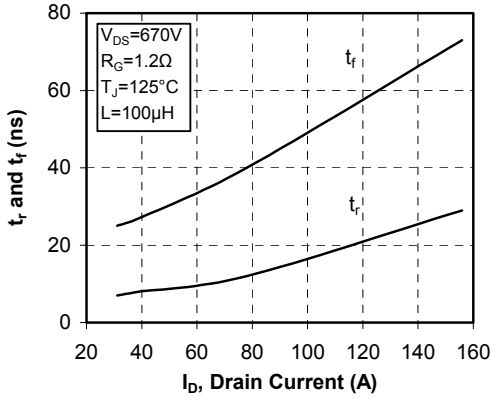

**Gate Charge vs Gate to Source Voltage**



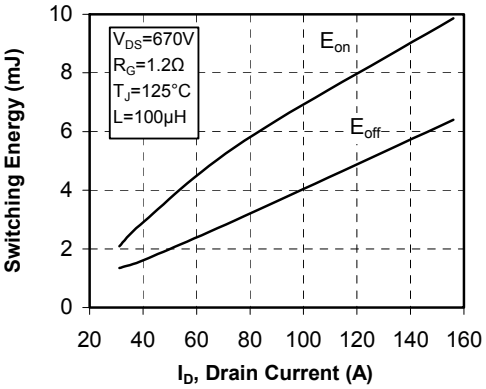
**Delay Times vs Current**



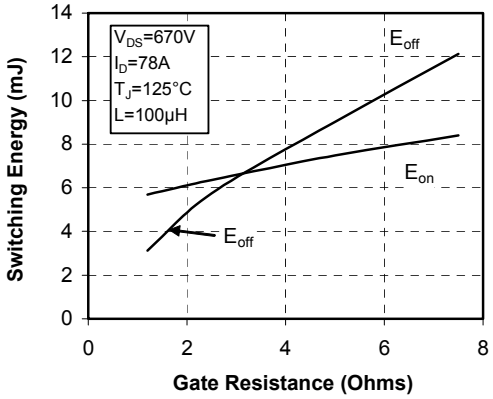

**Rise and Fall times vs Current**



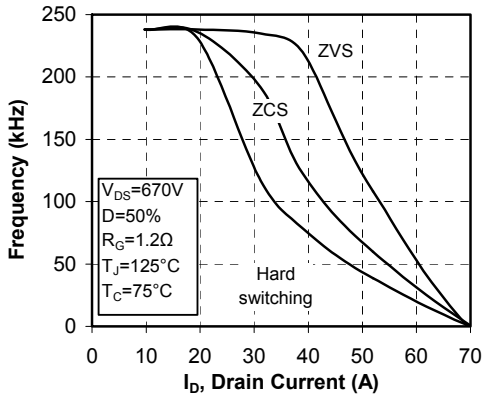

**Switching Energy vs Current**



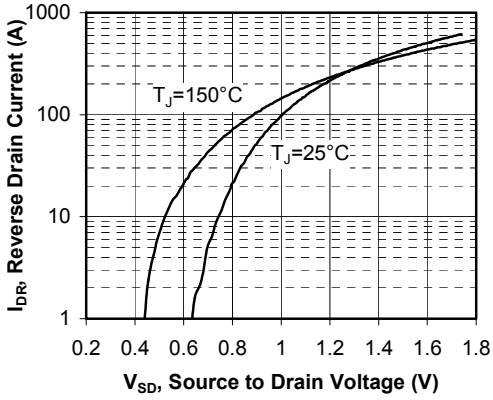

**Switching Energy vs Gate Resistance**




**Operating Frequency vs Drain Current**




**Source to Drain Diode Forward Voltage**



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